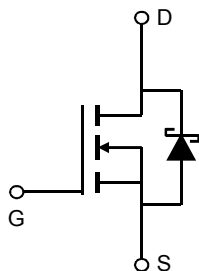
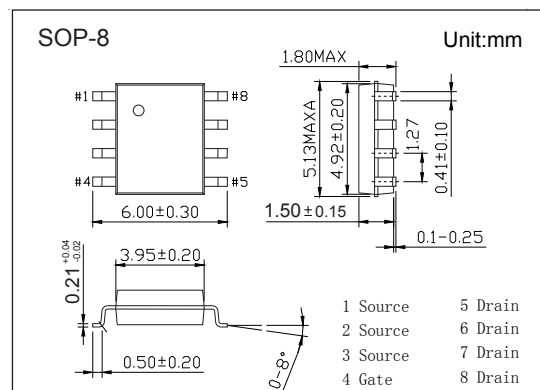


N-Channel MOSFET

AO4712 (KO4712)

■ Features

- $V_{DS} = 30V$
- $I_D = 13 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 11m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 14m\Omega$ ($V_{GS} = 4.5V$)
- SRFET™ Soft Recovery MOSFET: Integrated Schottky Diode

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current	$T_A = 25^\circ C$	I_D	13	A
	$T_A = 70^\circ C$		10	
Pulsed Drain Current		I_{DM}	68	
Avalanche Current		I_{AS}, I_{AR}	15	mJ
Repetitive Avalanche Energy	$L = 0.1mH$	E_{AS}, E_{AR}	11	
Power Dissipation	$T_A = 25^\circ C$	P_D	3.1	W
	$T_A = 70^\circ C$		2	
Thermal Resistance.Junction- to-Ambient	$t \leq 10s$	R_{thJA}	40	$^\circ C/W$
	Steady-State		75	
Thermal Resistance.Junction- to-Lead		R_{thJL}	24	$^\circ C$
Junction Temperature		T_J	150	
Storage Temperature Range		T_{stg}	-55 to 150	

N-Channel MOSFET

AO4712 (KO4712)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =1mA, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			0.5	mA
		V _{DS} =30V, V _{GS} =0V, T _J =125°C			100	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 μA	1.1		2.1	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =13A			11	mΩ
		V _{GS} =10V, I _D =13A, T _J =125°C			16	
		V _{GS} =4.5V, I _D =11A			14	
On State Drain Current	I _{D(on)}	V _{GS} =10V, V _{DS} =5V	68			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =13A		80		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz	930		1400	pF
Output Capacitance	C _{oss}		90		170	
Reverse Transfer Capacitance	C _{rss}		45		125	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.7		2.1	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =13A	16		24	nC
Total Gate Charge (4.5V)			7		10.5	
Gate Source Charge	Q _{gs}			3.2		
Gate Drain Charge	Q _{gd}			3		
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{DS} =15V, R _L =1.2Ω, R _{GEN} =3Ω		6		ns
Turn-On Rise Time	t _r			2.4		
Turn-Off DelayTime	t _{d(off)}			23		
Turn-Off Fall Time	t _f			4		
Body Diode Reverse Recovery Time	t _{rr}	I _F =13A, di/dt=500A/us	5.5		8.5	nC
Body Diode Reverse Recovery Charge	Q _{rr}		5		8	
Maximum Body-Diode Continuous Current	I _S				5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			0.7	V

Note. The static characteristics in Figures 1 to 6 are obtained using <300 us pulses, duty cycle 0.5% max.

■ Marking

Marking	4712 KC****
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N-Channel MOSFET

AO4712 (KO4712)

■ Typical Characteristics

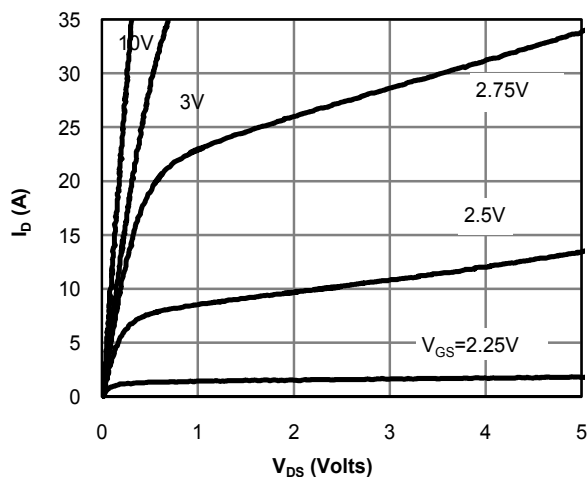


Fig 1: On-Region Characteristics (Note E)

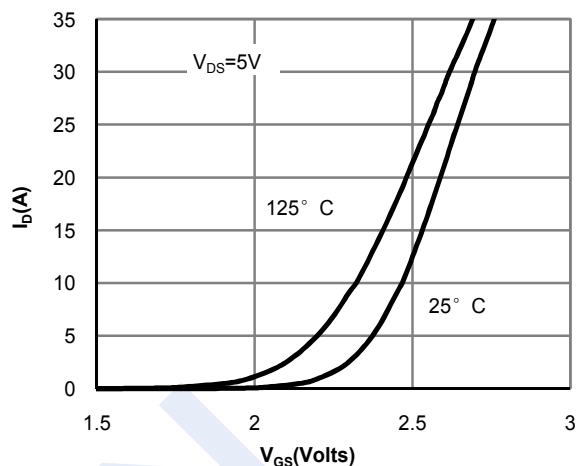


Figure 2: Transfer Characteristics (Note E)

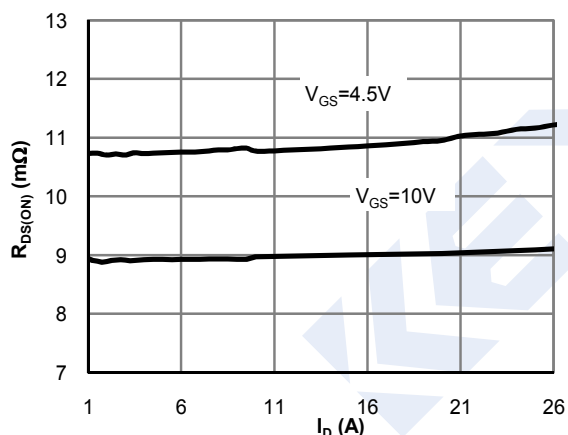


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

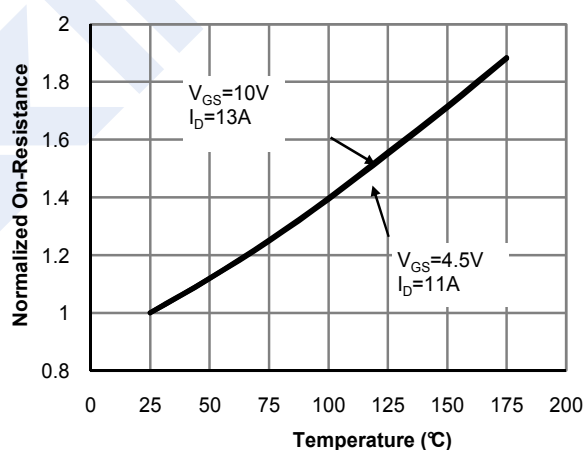


Figure 4: On-Resistance vs. Junction Temperature (Note E)

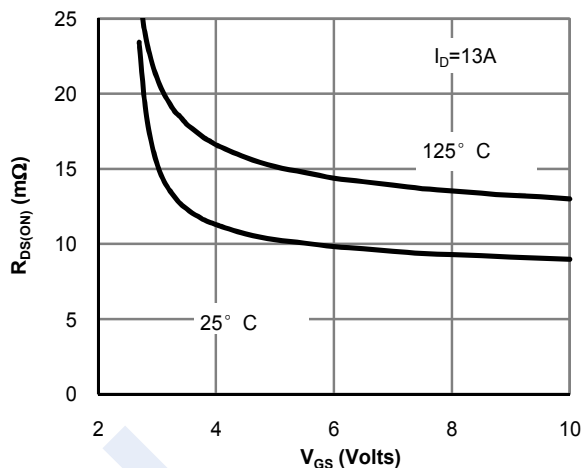


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

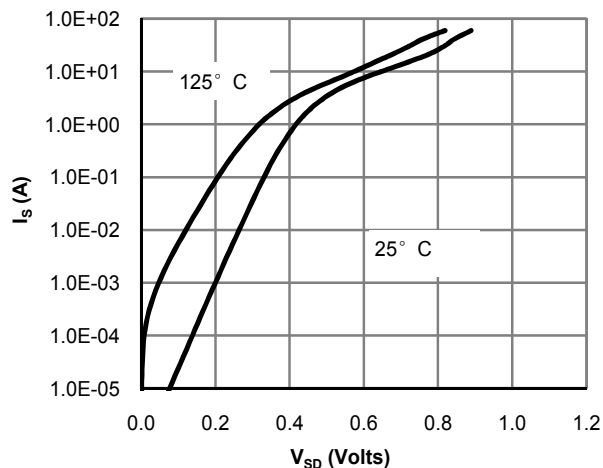


Figure 6: Body-Diode Characteristics (Note E)

N-Channel MOSFET

AO4712 (KO4712)

■ Typical Characteristics

